

Kindly amend the specification as follows:

Page 5 line 10 erase the cross hatched ~~the bulk~~

line 11 erase the cross hatched ~~frame 4~~ and in lieu thereof insert the underlined layer 5 and,

line 12 erase the cross hatched ~~layer 5~~ and in lieu thereof insert the underlined frame 4 , as follows.

-- For example, where the semiconductor that is to be the ~~frame 4~~ layer 5 would have a doping level of about 7×10^{19} atoms / Cm³ then the doping level of the ~~layer 5~~ frame 4 would be about 10^{16} atoms/Cm³ --

The clean amended paragraph is:

--A difference in etch responsiveness capability, of the portion of the wafer that is to become the layer 5, with respect to the bulk portion that is to become the frame 4, is imparted by diffusion or growing through or on the surface 1, so as to produce a crystalline layer about 1- 10 micrometers thick of heavily doped semiconductor material. For example, where the semiconductor that is to be the layer 5 would have a doping level of about 7×10^{19} atoms / Cm³ then the doping level of the frame 4 would be about 10^{16} atoms/Cm³ --